



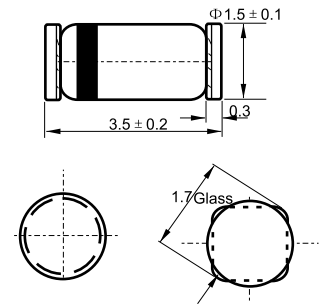
Reverse Voltage:60-70Volts

Forward Current:10.0Amps

Features

- ✧ For general purpose applications.
- ✧ Metal-on-silicon schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.

MINI MELF



Dimension in millimeters

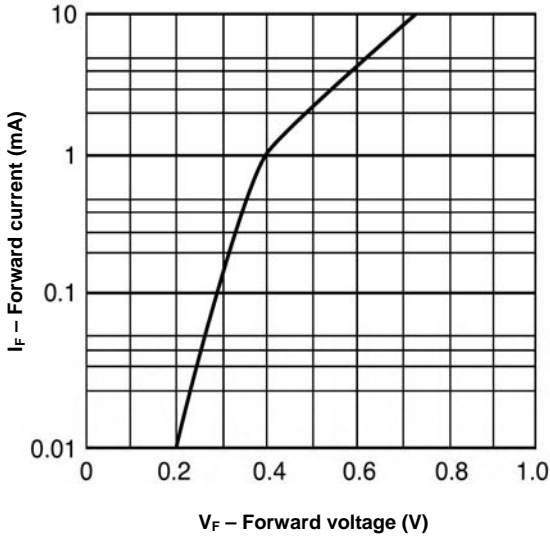
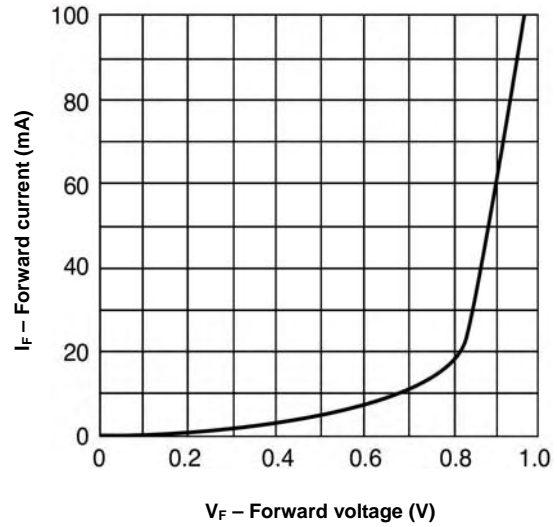
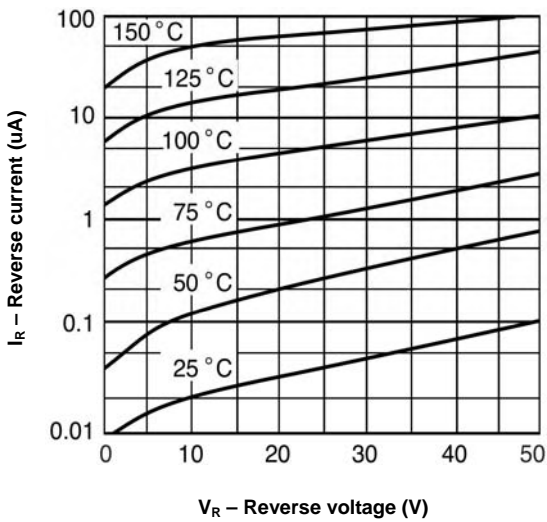
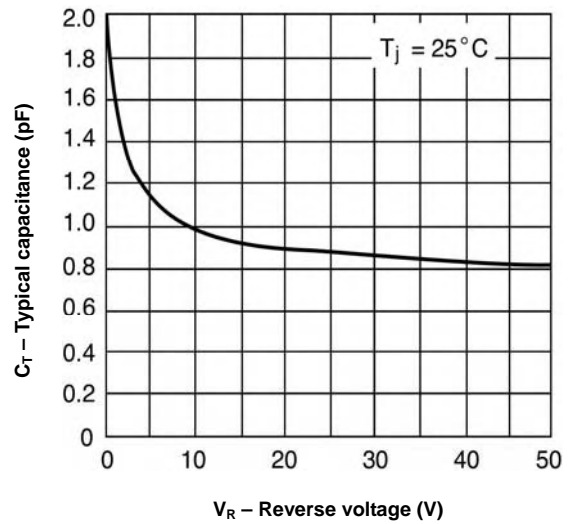
Absolute Maximum Ratings (T_j=25°C)

Parameter	Part	Symbol	Value	Unit
Peak inverse voltage	LL5711	V _{RRM}	70	V
	LL6263	V _{RRM}	60	V
Maximum single cycle surge 10us square wave		I _{FSM}	2.0	A
Power dissipation		P _{tot}	400	mW
Maximum junction temperature		T _j	125	°C
Storage temperature range		T _s	-55~+150	°C

Electrical Characteristics(T_j=25°C)

Parameter	Symbol	Test Conditions	Part	Min	Typ	Max	Unit
Reverse breakdown voltage	V _{(BR)R}	I _R =10 μ A (pulsed)	LL5711	70	-	-	V
			LL6263	60	-	-	v
Leakage current	I _R	V _R =50V		-	-	200	nA
Forward voltage drop	V _F	I _F =1mA		-	-	0.41	V
		I _F =15mA		-	-	1.0	V
Junction capacitance	C _{tot}	V _R =0V, f=1MHz	LL5711	-	-	2.0	pF
			LL6263	-	-	2.2	pF
Reverse recovery time	t _{rr}	I _F = I _R =5mA recover to 0.1 I _R		-	-	1.0	ns

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.


Characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified)

Figure 1. Typical variation of forward current vs. forward voltage

Figure 2. Typical forward conduction curve

Figure 3. Typical variation of reverse current at various temperatures

Figure 4. Typical capacitance curve as a function of reverse voltage

Package	Reel	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
minimelf	2500pcs	7inch	20000pcs	186×186×105	120,000pcs	443×215×305